AP8205T

ROHS

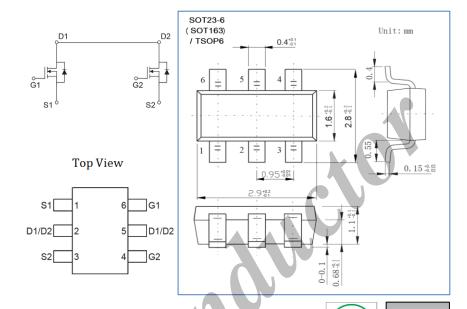
Semiconductor Dual N-Channel Enhancement Mode Power MOSFET

General Description

AP8205T combines advanced MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is most suitable to Li-ion battery management applications.

Applications

Li-ion battery management applications



Product Summary

 V_{DS} 20V

I_D 4.3A

RDS(ON) (at VGS = 4V) $< 30 \text{m}\Omega$

RDS(ON) (at VGS = 2.5V) < $46m\Omega$

• Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	VDS	20	V	
Gate-Source Voltage	Vgs	±12	V	
Drain Current-Continuous @ TA = 25 ℃ *1	ID	4.3	Α	
Drain Current-Continuou -Pulse *2	IDM	21.5	Α	
Drain-Source Diode Forward Current *1	Is	1.7	А	
Maximum Power Dissipation TA=25℃ *1	PD	1.25	W	
TA=75°C	PD	0.75	V V	
Operating Junction and Storage Temperature Range	TJ,TSTG	- 55 to 150	$^{\circ}$	
Thermal Resistance,Junction-to-Ambient	RthJA	100	°C/W	

^{*1} Surface Mounted on FR4 Board , t ≤ 10sec .

^{*2} Pulse width limited by maximum junction temperature.

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• Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	Voss	V_{GS} = 0V , I_{D} = 250 μ A	20			V
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 20V , V _{GS} = 0V			1	μА
Gate-Body Leakage	lgss	$V_{GS} = \pm 12 V$, $V_{DS} = 0 V$			±100	nA
Gate Threshold Voltage *1	VGS(th)	V _{DS} = V _{GS} , I _D = 250uA	0.45	. (1	V
Drain-Source On-State Resistance *1	RDS(on)	V _G S = 4V , I _D = 4.3A			30	mΩ
		$V_{GS} = 2.5V$, $I_D = 3.4A$		7	46	
Input Capacitance	Ciss			550		
Output Capacitance	Coss	$V_{DS} = 8V$, $V_{GS} = 0V$, $f = 1.0MHz$		164		рF
Reverse Transfer Capacitance	Crss			138		
Turn-On Delay Time	t d(on)	VDD = 10V , ID = 1A		10		ns
Turn-Off Delay Time	tr	V _{GEN} = 4.5V		8.2		ns
Rise Time	td(off)	RL = 10 Ω		25		ns
Fall Time	t f	RGEN = 6 Ω		6.7		ns
Total Gate Charge	Qg			6.2		nC
Gate-Source Charge	Qgs	$V_{DS} = 10V$, $I_{D} = 3A, V_{GS} = 4.5V$		1.8		nC
Gate-Drain Charge	Qgd			1.5		nC
Diode Forward Voltage	VsD	V _G S = 0V , I _S = 1.7A *1			1.2	V

^{*1} Pulse width \leqslant 300 μ s , Duty Cycle \leqslant 2% .

Ordering Information

Ordering Part Number	Package	MOQ
AP8205T	SOT23-6 (SOT163)	3,000 pcs / reel

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